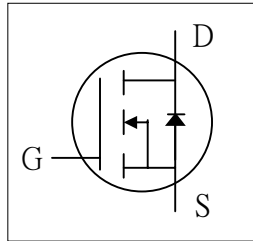




- ▼ 100% Avalanche Test
- ▼ Fast Switching Characteristic
- ▼ Simple Drive Requirement

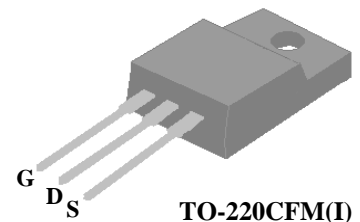


$BV_{DSS}$	600V
$R_{DS(ON)}$	2.4 $\Omega$
$I_D$	4A

## Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220CFM isolation package is widely preferred for all commercial-industrial through hole applications.



TO-220CFM(I)

## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	600	V
$V_{GS}$	Gate-Source Voltage	+30	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V	4	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V	2.5	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	15	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	33	W
	Linear Derating Factor	0.26	W/ $^\circ\text{C}$
$E_{AS}$	Single Pulse Avalanche Energy <sup>2</sup>	8	mJ
$I_{AR}$	Avalanche Current	4	A
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

## Thermal Data

Symbol	Parameter	Value	Unit
Rthj-c	Maximum Thermal Resistance, Junction-case	3.8	$^\circ\text{C}/\text{W}$
Rthj-a	Maximum Thermal Resistance, Junction-ambient	65	$^\circ\text{C}/\text{W}$


**Electrical Characteristics @ $T_j=25^\circ\text{C}$  (unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=1mA$	600	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=1mA$	-	0.6	-	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>3</sup>	$V_{GS}=10V, I_D=2A$	-	-	2.4	$\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	-	4	V
$g_{fs}$	Forward Transconductance	$V_{DS}=10V, I_D=2A$	-	2.5	-	S
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=600V, V_{GS}=0V$	-	-	10	$\mu A$
	Drain-Source Leakage Current ( $T_j=125^\circ\text{C}$ )	$V_{DS}=480V, V_{GS}=0V$	-	-	500	$\mu A$
$I_{GSS}$	Gate-Source Leakage	$V_{GS}=\pm 30V, V_{DS}=0V$	-	-	$\pm 100$	nA
$Q_g$	Total Gate Charge <sup>3</sup>	$I_D=4A$	-	16.7	-	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS}=480V$	-	4.1	-	nC
$Q_{gd}$	Gate-Drain ("Miller") Charge	$V_{GS}=10V$	-	4.9	-	nC
$t_{d(on)}$	Turn-on Delay Time <sup>3</sup>	$V_{DD}=300V$	-	11	-	ns
$t_r$	Rise Time	$I_D=4A$	-	8.3	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=10\Omega, V_{GS}=10V$	-	23.8	-	ns
$t_f$	Fall Time	$R_D=75\Omega$	-	8.2	-	ns
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	-	950	-	pF
$C_{oss}$	Output Capacitance	$V_{DS}=25V$	-	65	-	pF
$C_{rss}$	Reverse Transfer Capacitance	$f=1.0MHz$	-	6	-	pF

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$I_S$	Continuous Source Current ( Body Diode )	$V_D=V_G=0V, V_S=1.5V$	-	-	4	A
$I_{SM}$	Pulsed Source Current ( Body Diode ) <sup>1</sup>		-	-	15	A
$V_{SD}$	Forward On Voltage <sup>3</sup>	$T_j=25^\circ\text{C}, I_S=4A, V_{GS}=0V$	-	-	1.5	V

**Notes:**

1. Pulse width limited by max. junction temperature
2. Starting  $T_j=25^\circ\text{C}$ ,  $V_{DD}=50V$ ,  $L=1mH$ ,  $R_G=25\Omega$ ,  $I_{AS}=4A$ .
3. Pulse test

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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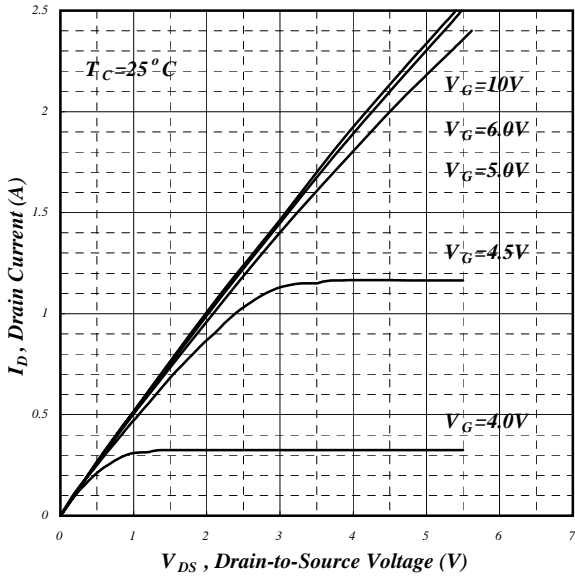


Fig 1. Typical Output Characteristics

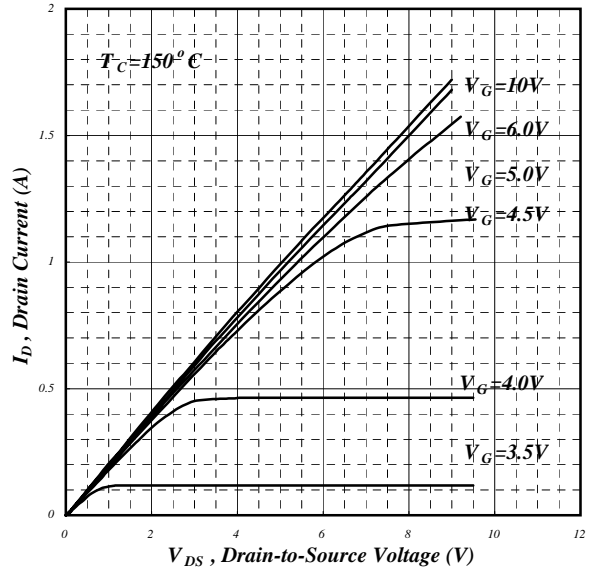


Fig 2. Typical Output Characteristics

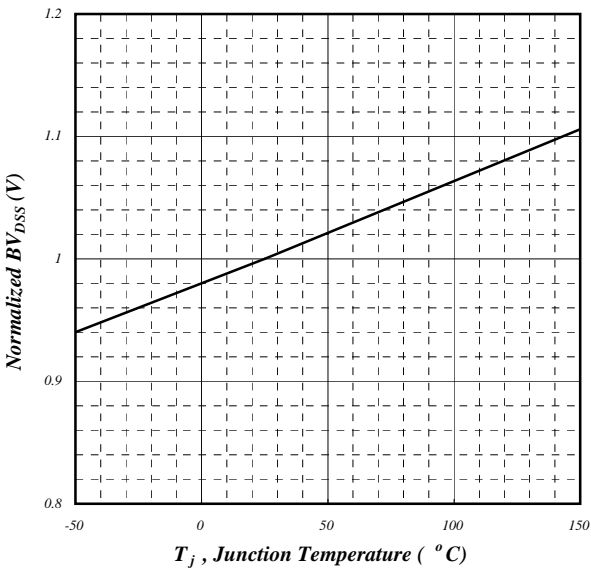


Fig 3. Normalized  $BV_{DSS}$  v.s. Junction Temperature

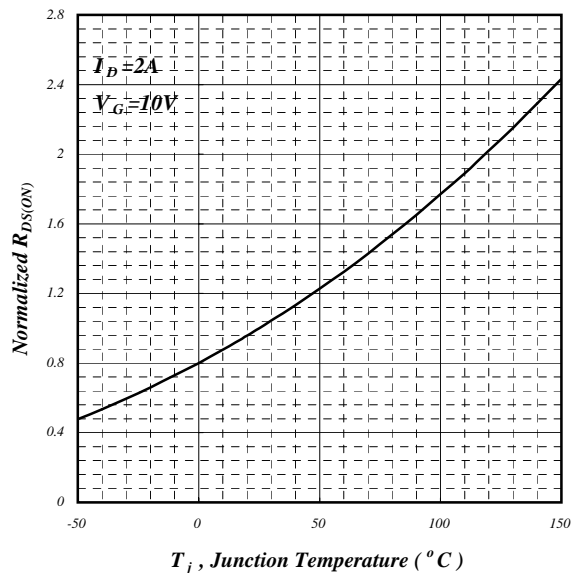


Fig 4. Normalized On-Resistance v.s. Junction Temperature

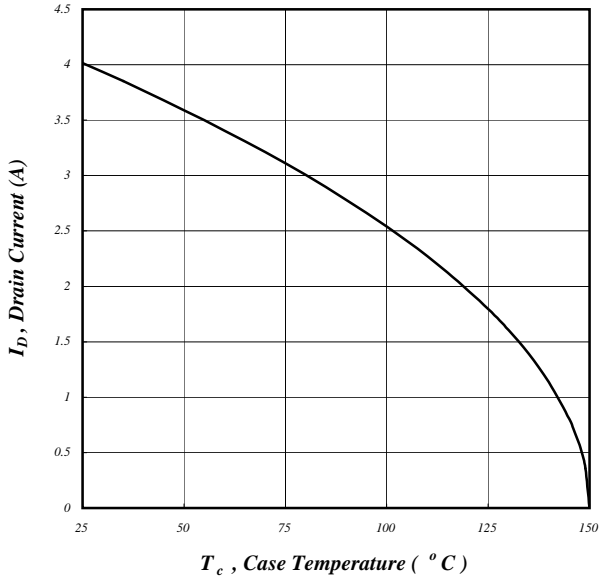


Fig 5. Maximum Drain Current v.s. Case Temperature

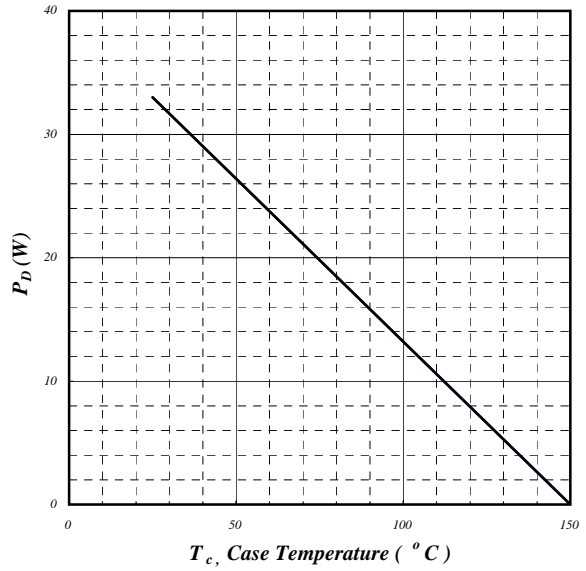


Fig 6. Typical Power Dissipation

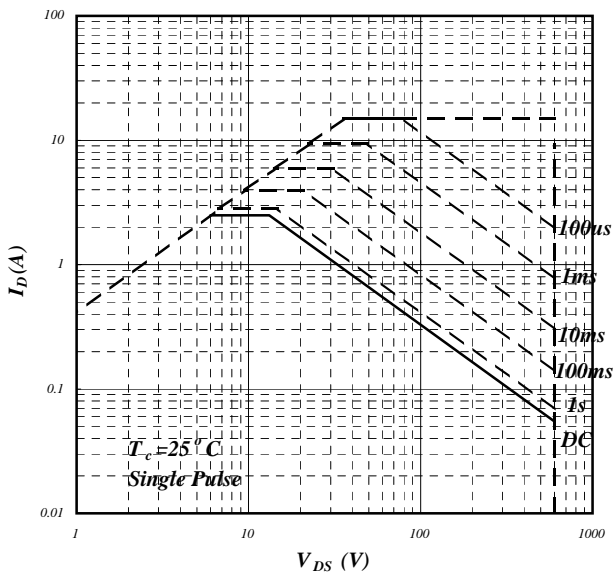


Fig 7. Maximum Safe Operating Area

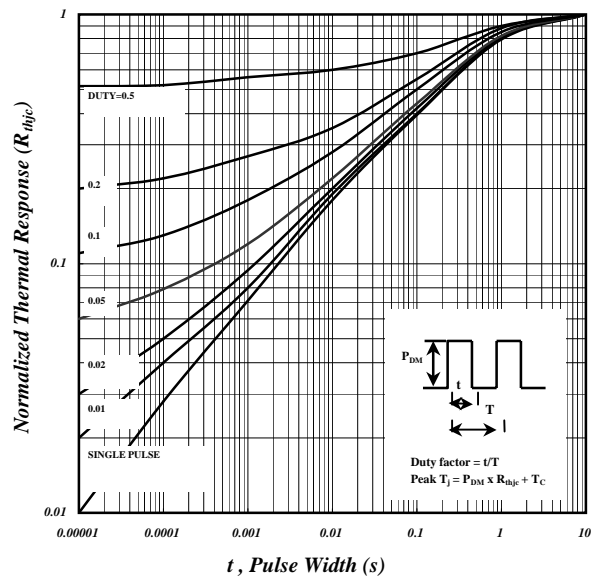


Fig 8. Effective Transient Thermal Impedance

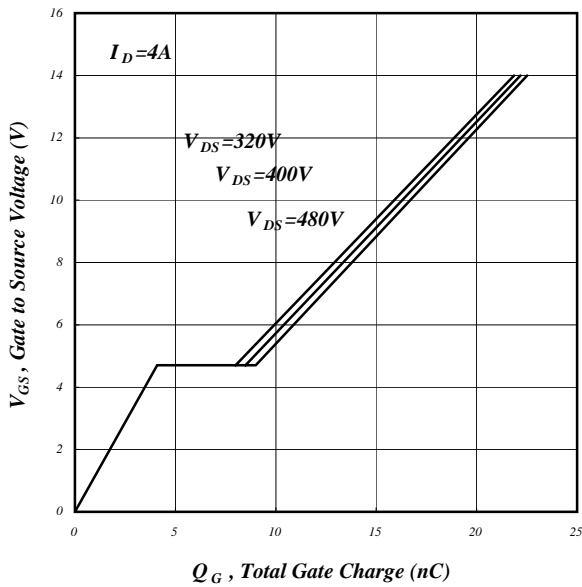


Fig 9. Gate Charge Characteristics

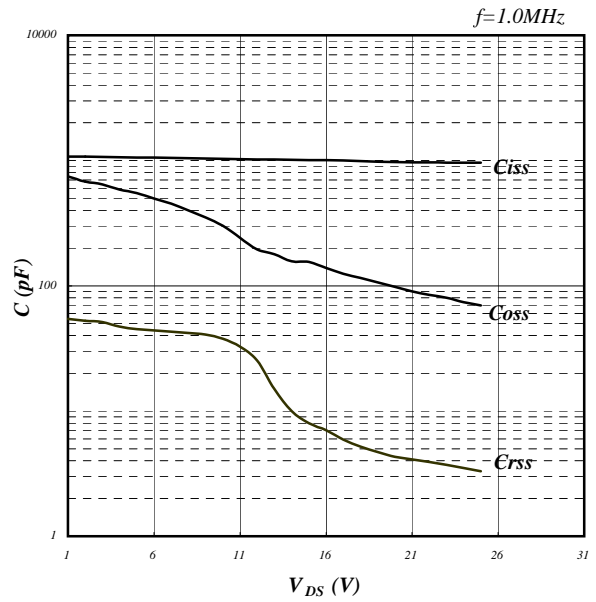


Fig 10. Typical Capacitance Characteristics

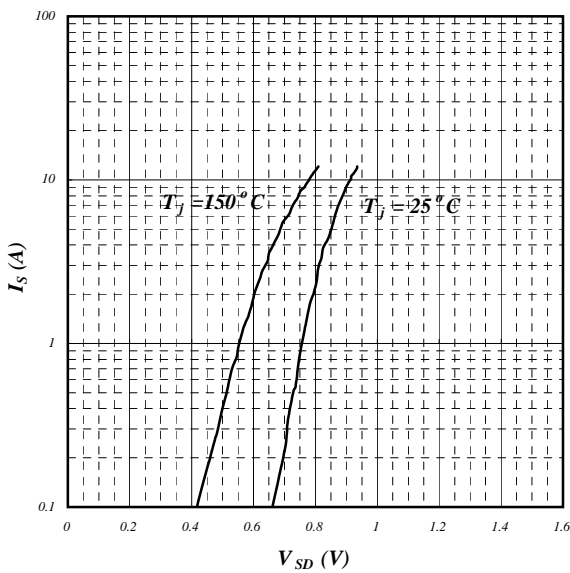


Fig 11. Forward Characteristic of Reverse Diode

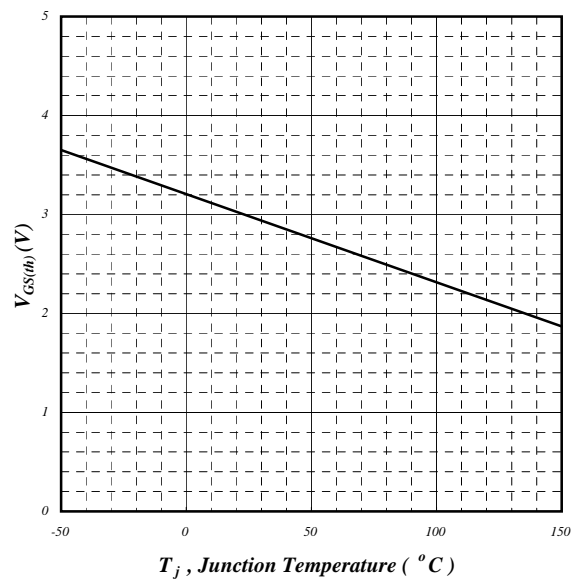


Fig 12. Gate Threshold Voltage v.s. Junction Temperature

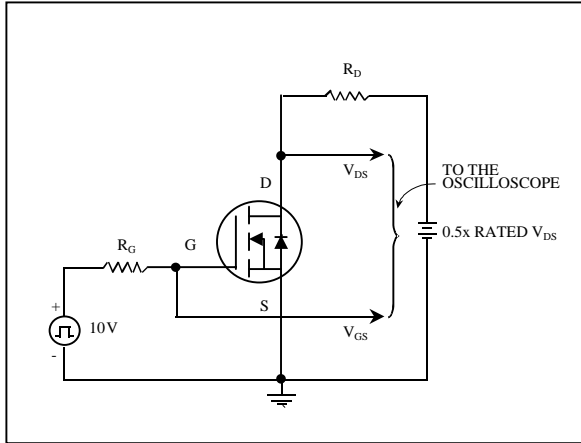


Fig 13. Switching Time Circuit

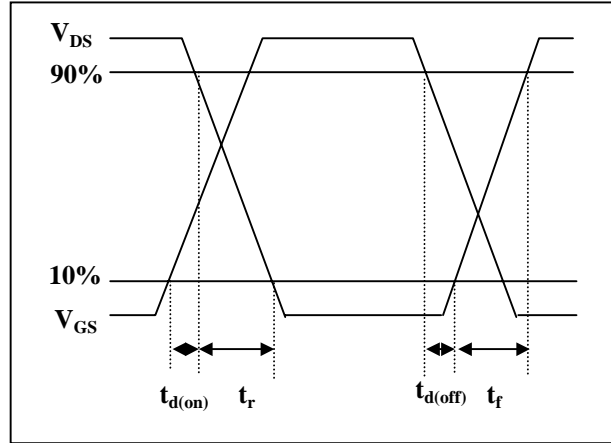


Fig 14. Switching Time Waveform

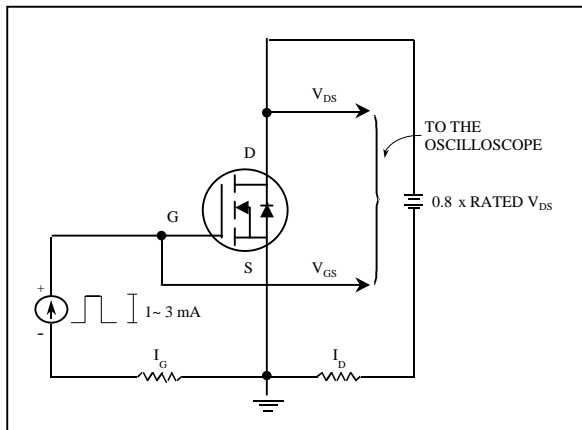


Fig 15. Gate Charge Circuit

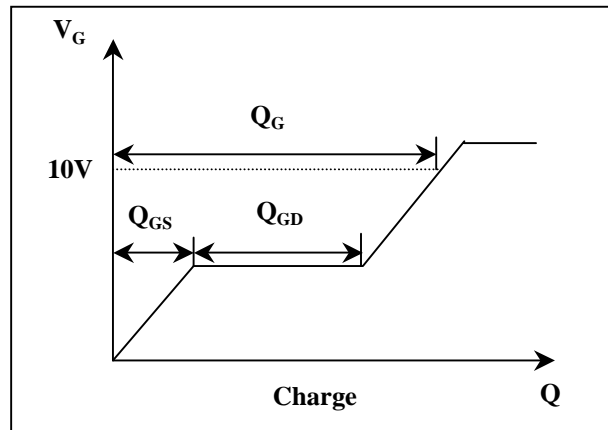


Fig 16. Gate Charge Waveform